

3DD164(166), 3DD167(169)**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications					
			3DD164			3DD167		
			A	B	C	D	E	F
Collector-Emitter Voltage	V_{CEO}	V	50	100	150	200	250	300
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	50	100	150	200	250	300
C-Base Breakdown Voltage	$V_{(BR)CBO}$	V	3DD164: $I_C=5mA$			3DD167: $I_C=5mA$		
			80	150	200	250	350	400
Emitter-Base Voltage	V_{EBO}	V	5			5		
Max. Collector Current	I_{CM}	A	10			15		
Max. Collector Dissipation	P_{CM}	W	100 ($T_c \leq 75^\circ C$)			150 ($T_c \leq 75^\circ C$)		
Junction Temperature	T_{jm}	$^\circ C$	175					
Storage Temperature	T_{stg}	$^\circ C$	-55~+175					
Collector-Emitter Leakage Current	I_{CEO}	mA	2.0 (A: $V_{CE}=30V$; B: $V_{CE}=50V$; C~F: $V_{CE}=100V$)					
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.5 ($I_C=5A, I_B=0.5A$)			1.5 ($I_C=7.5A, I_B=0.75A$)		
DC Current Gain	h_{FE}		Max.:180,Min.:15 ($V_{CE}=5V, I_C=5A$)			Max.:180, Min.:15 ($V_{CE}=5V, I_C=7.5A$)		
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 5 ($I_E=5mA$)			≥ 5 ($I_E=10mA$)		

h_{FE} Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	15~25	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions: